Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	3.9	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 3.9 \text{ A}; T_j = 25 \text{ °C}$		-	30	43	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV50ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV50ENEA	DV%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j = 25 °C		-	30	V
gate-source voltage			-20	20	V
drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	3.9	Α
	V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	2.5	Α
peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	15.5	Α
non-repetitive drain-source avalanche energy	T _{j(init)} = 25 °C; I _D = 0.6 A; DUT in avalanche (unclamped)		-	9	mJ
total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
		[1]	-	1.04	W
	T _{sp} = 25 °C		-	3.9	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
liode					,
source current	T _{amb} = 25 °C	[1]	-	1	Α
rating		'		'	,
electrostatic discharge voltage	НВМ	[3]	-	2000	V
	drain-source voltage gate-source voltage drain current peak drain current non-repetitive drain-source avalanche energy total power dissipation junction temperature ambient temperature storage temperature liode source current rating	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} drain\text{-source voltage} \\ gate\text{-source voltage} \\ drain current \\ \hline \\ & V_{GS} = 10 \text{ V; } T_{amb} = 25 \text{ °C} \\ \hline \\ & V_{GS} = 10 \text{ V; } T_{amb} = 25 \text{ °C} \\ \hline \\ & V_{GS} = 10 \text{ V; } T_{amb} = 100 \text{ °C} \\ \hline \\ & I1 \\ \hline \\ & peak drain current \\ \hline \\ & rating \\ \hline \\ & T_{ij} = 25 \text{ °C} \\ \hline \\ & V_{GS} = 10 \text{ V; } T_{amb} = 100 \text{ °C} \\ \hline \\ & I1 \\ \hline \\ & V_{GS} = 10 \text{ V; } T_{amb} = 100 \text{ °C} \\ \hline \\ & I1 \\ \hline \\ & V_{GS} = 10 \text{ V; } T_{amb} = 25 \text{ °C; single pulse; } t_p \leq 10 \text{ µs} \\ \hline \\ & I1 \\ \hline \\ & I1 \\ \hline \\ & I2 \\ \hline \\ & I1 \\ \hline \\ & I3 \\ \hline \\ & I2 \\ \hline \\ & I1 \\ \hline \\ & I3 \\ \hline \\ & I3 \\ \hline \\ & I4 \\ \hline \\ & I2 \\ \hline \\ & I2 \\ \hline \\ & I3 \\ \hline \\ & I3 \\ \hline \\ & I4 \\ \hline \\ & I5 \\ \hline \\ \\ \\ & I5 \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	$ \begin{array}{c} drain\text{-source voltage} \\ gate\text{-source voltage} \\ drain current \\ \hline \\ V_{GS} = 10 \text{ V; } T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ V_{GS} = 10 \text{ V; } T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ V_{GS} = 10 \text{ V; } T_{amb} = 100 ^{\circ}\text{C} \\ \hline \\ I11 \\ \hline \\ Peak drain current \\ \hline \\ peak drain current \\ \hline \\ T_{amb} = 25 ^{\circ}\text{C; single pulse; } t_p \leq 10 \mu\text{s} \\ \hline \\ \\ 10 \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	$ \begin{array}{c} \mbox{drain-source voltage} \\ \mbox{gate-source voltage} \\ \mbox{qate-source voltage} \\ \mbox{drain current} \\ & V_{GS} = 10 \ V; \ T_{amb} = 25 \ ^{\circ}C \\ & V_{GS} = 10 \ V; \ T_{amb} = 25 \ ^{\circ}C \\ & V_{GS} = 10 \ V; \ T_{amb} = 100 \ ^{\circ}C \\ & [1] \\ & - \\ & 2.5 \\ \\ \mbox{peak drain current} \\ & T_{amb} = 25 \ ^{\circ}C; \ single \ pulse; \ t_p \leq 10 \ \mu s \\ & - \\ & 15.5 \\ \\ & - \\ & 15.5 \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \mbox$

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

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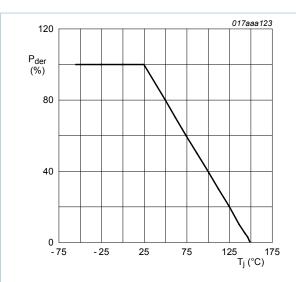


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

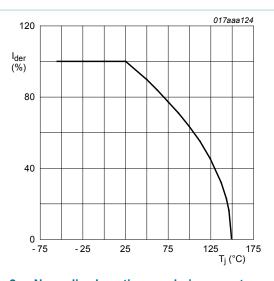


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

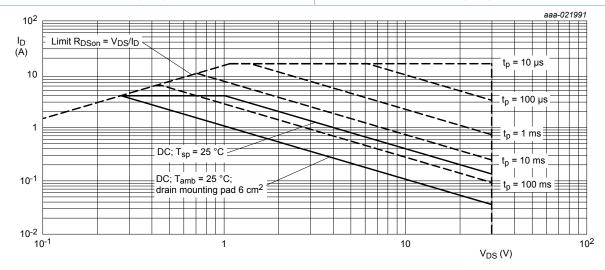


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

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Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
froi	thermal resistance from junction to ambient		[1]	-	211	245	K/W
			[2]	-	102	120	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	21	32	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

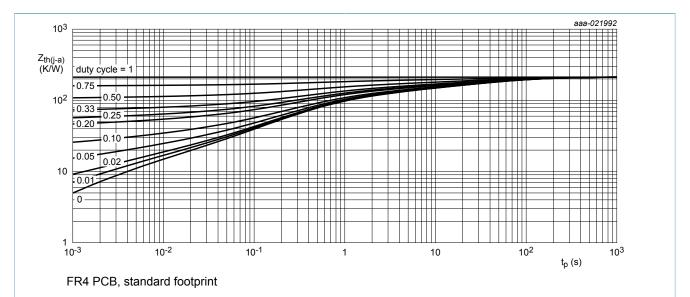


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

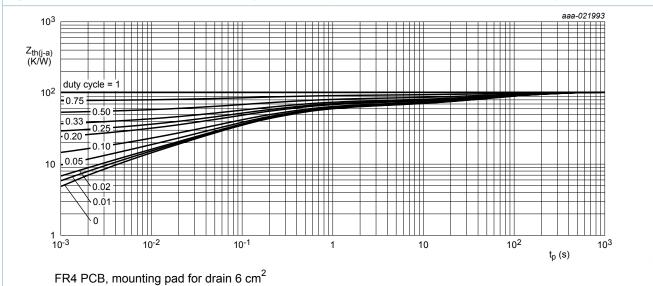


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	1	1.5	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 3.9 A; T _j = 25 °C	-	30	43	mΩ
	resistance	V _{GS} = 10 V; I _D = 3.9 A; T _j = 150 °C	-	48	69	mΩ
		V_{GS} = 4.5 V; I_D = 3.3 A; T_j = 25 °C	-	39	60	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 3.9 A; T_j = 25 °C	-	12.5	-	S
R _G	gate resistance	f = 1 MHz	-	7	-	Ω
Dynamic cl	haracteristics	1				
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_{D} = 3.9 A; V_{GS} = 10 V;	-	6	10	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.6	-	nC
Q_{GD}	gate-drain charge		-	1.2	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	276	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	55	-	pF
C _{rss}	reverse transfer capacitance		-	42	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 3.9 A; V _{GS} = 10 V;	-	6.3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	17.3	-	ns
t _{d(off)}	turn-off delay time		-	14.1	-	ns
t _f	fall time		-	6.6	-	ns
Source-dra	in diode	1	1		1	
V _{SD}	source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

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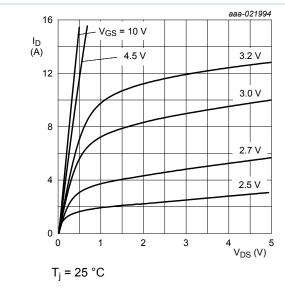


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

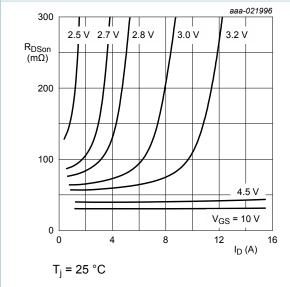


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

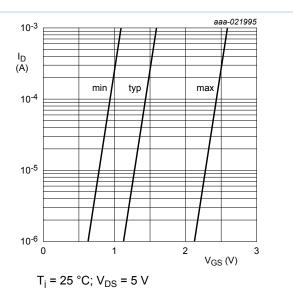


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

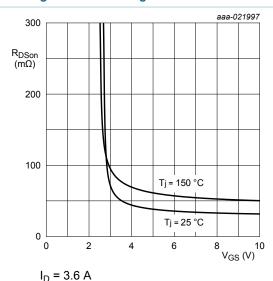
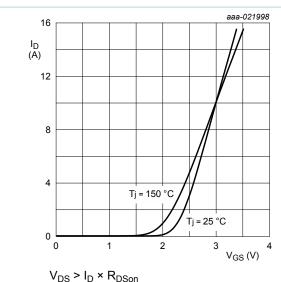


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



V_{DS} > I_D × K_{DSon}

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

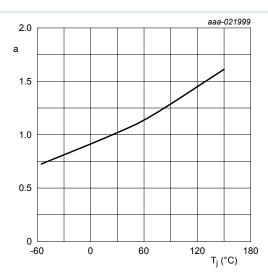


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

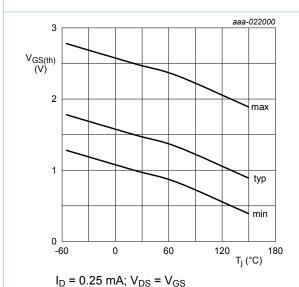
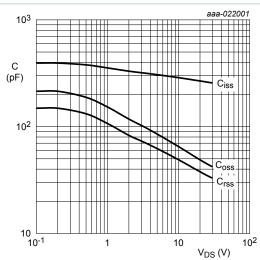


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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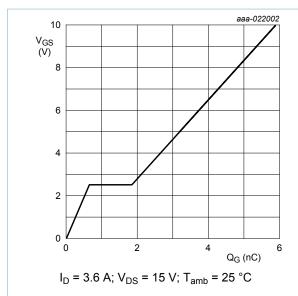


Fig. 14. Gate-source voltage as a function of gate charge; typical values

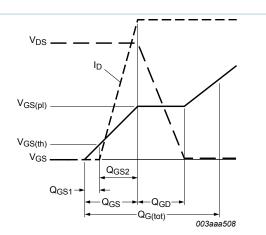


Fig. 15. MOSFET transistor: Gate charge waveform definitions

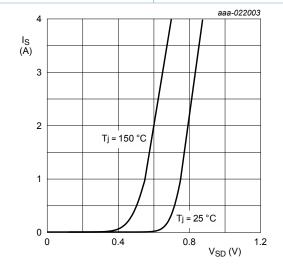
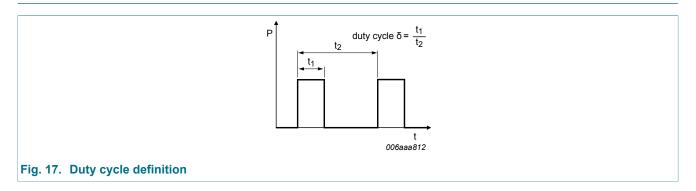


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information

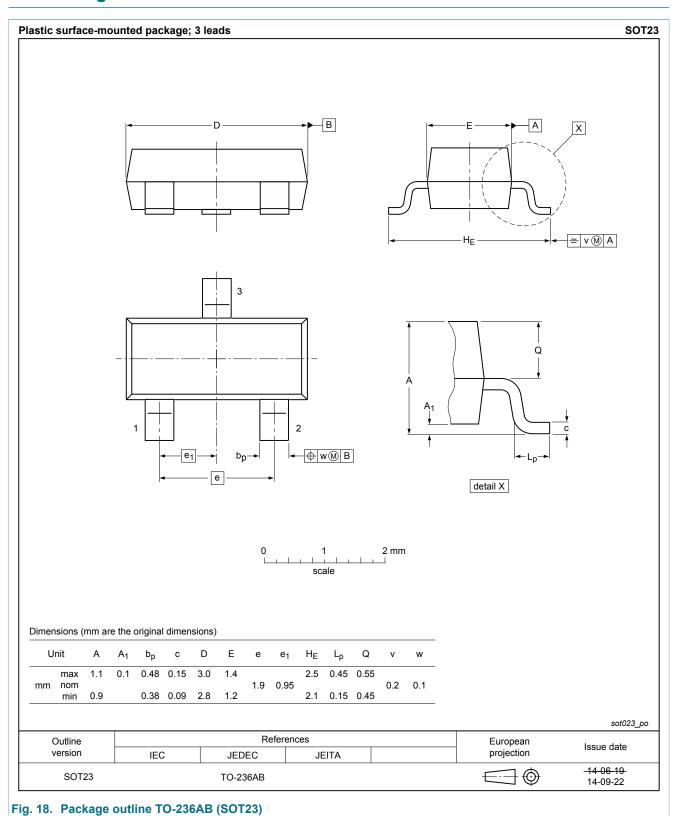


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline

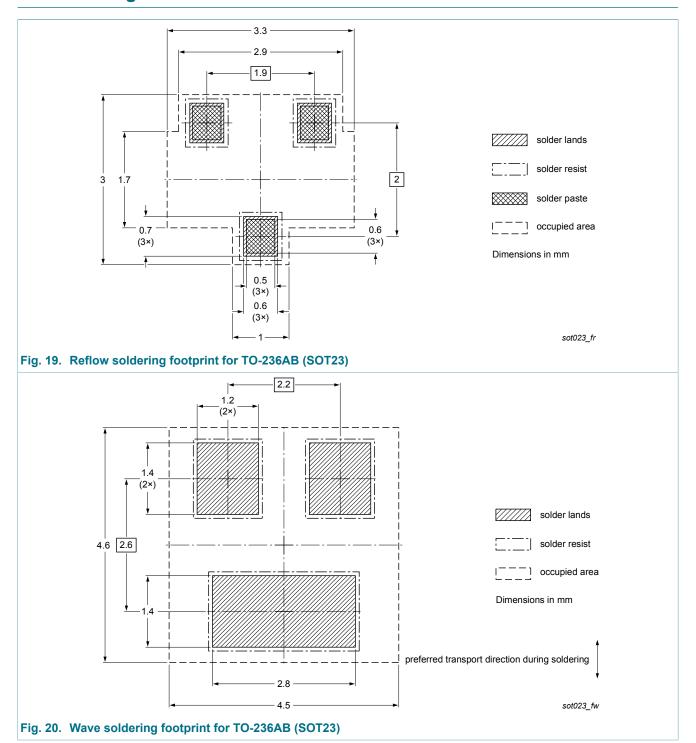


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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV50ENEA v.1	20160310	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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